

5SNA 1300K450300

StakPak IGBT Module

$V_{CE} = 4500 \text{ V}$
 $I_C = 1300 \text{ A}$

Fails into stable shorted state
 Low-loss, rugged SPT+ chip-set
 Smooth switching SPT+ chip-set for good EMC
 High tolerance to uneven mounting pressure
 Explosion resistant package



Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	max	Unit
Collector-emitter voltage	V_{CES}	$V_{GE} = 0 \text{ V}$, $T_{vj} \geq 25 \text{ °C}$		4500	V
DC collector current	I_C	$T_C = 85 \text{ °C}$, $T_{vj} = 125 \text{ °C}$		1300	A
Peak collector current	I_{CM}	$t_p = 1 \text{ ms}$		2600	A
Gate-emitter voltage	V_{GES}		-20	20	V
Total power dissipation	P_{tot}	$T_C = 25 \text{ °C}$, $T_{vj} = 125 \text{ °C}$		16700	W
DC forward current	I_F			1300	A
Peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$		2600	A
Surge current	I_{FSM}	$V_R = 0 \text{ V}$, $T_{vj} = 125 \text{ °C}$, $t_p = 10 \text{ ms}$, half-sinewave		21000	A
IGBT short circuit SOA	t_{psc}	$V_{CC} = 3400 \text{ V}$, $V_{CEM \text{ CHIP}} \leq 4500 \text{ V}$ $V_{GE} \leq 15 \text{ V}$, $T_{vj} \leq 125 \text{ °C}$		10	μs
Junction temperature	T_{vj}		-50	150	$^{\circ}\text{C}$
Junction operating temperature	$T_{vj(op)}$		-50	125	$^{\circ}\text{C}$
Case temperature	T_C		-50	125	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-50	70	$^{\circ}\text{C}$
Mounting force ²⁾³⁾	F_M		60	90	kN

¹⁾ Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747

²⁾ For detailed mounting instructions refer to ABB document no. 5SYA 2037-02

³⁾ All electrical characteristics are valid only when the module is clamped

IGBT characteristic values ⁴⁾

Parameter	Symbol	Conditions	min	typ	max	Unit	
Collector (-emitter) breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$, $I_C = 10 \text{ mA}$, $T_{vj} = 25 \text{ }^\circ\text{C}$	4500			V	
Collector-emitter ⁵⁾ saturation voltage	$V_{CE \text{ sat}}$	$I_C = 1300 \text{ A}$, $V_{GE} = 15 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	2.7	3.0	V	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	3.4	3.7	V	
Collector cut-off current	I_{CES}	$V_{CE} = 4500 \text{ V}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^\circ\text{C}$		1	mA	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	55	80	mA	
Gate leakage current	I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$, $T_{vj} = 125 \text{ }^\circ\text{C}$	-500		500	nA	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C = 240 \text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25 \text{ }^\circ\text{C}$	5.3		7.3	V	
Gate charge	Q_G	$I_C = 1300 \text{ A}$, $V_{CE} = 2800 \text{ V}$, $V_{GE} = -15 \text{ V} \dots 15 \text{ V}$		6.4		μC	
Input capacitance	C_{ies}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$, $T_{vj} = 25 \text{ }^\circ\text{C}$		140		nF	
Output capacitance	C_{oes}				10		nF
Reverse transfer capacitance	C_{res}				2.8		nF
Internal gate resistor	R_{Gint}			0.21		Ω	
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 2800 \text{ V}$, $I_C = 1300 \text{ A}$, $R_G = 1.8 \text{ } \Omega$, $C_{GE} = 330 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_\sigma = 200 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^\circ\text{C}$	600		ns	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	720		ns	
Rise time	t_r	$V_{CC} = 2800 \text{ V}$, $I_C = 1300 \text{ A}$, $R_G = 1.8 \text{ } \Omega$, $C_{GE} = 330 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_\sigma = 200 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^\circ\text{C}$	500		ns	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	600		ns	
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 2800 \text{ V}$, $I_C = 1300 \text{ A}$, $R_G = 8.2 \text{ } \Omega$, $C_{GE} = 330 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_\sigma = 200 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^\circ\text{C}$	3300		ns	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	3700		ns	
Fall time	t_f	$V_{CC} = 2800 \text{ V}$, $I_C = 1300 \text{ A}$, $R_G = 8.2 \text{ } \Omega$, $C_{GE} = 330 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_\sigma = 200 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^\circ\text{C}$	700		ns	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	680		ns	
Turn-on switching energy	E_{on}	$V_{CC} = 2800 \text{ V}$, $I_C = 1300 \text{ A}$, $R_G = 1.8 \text{ } \Omega$, $C_{GE} = 330 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_\sigma = 200 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^\circ\text{C}$	3500		mJ	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	5000		mJ	
Turn-off switching energy	E_{off}	$V_{CC} = 2800 \text{ V}$, $I_C = 1300 \text{ A}$, $R_G = 8.2 \text{ } \Omega$, $C_{GE} = 330 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_\sigma = 200 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^\circ\text{C}$	5500		mJ	
			$T_{vj} = 125 \text{ }^\circ\text{C}$	7000		mJ	
Short circuit current	I_{sc}	$t_{psc} \leq 10 \text{ } \mu\text{s}$, $V_{GE} = 15 \text{ V}$, $V_{CC} = 3400 \text{ V}$, $V_{CEM \text{ CHIP}} \leq 4500 \text{ V}$		6000		A	

⁴⁾ Characteristic values according to IEC 60747 - 9

⁵⁾ Collector-emitter saturation voltage is given at chip level

Diode characteristic values ⁶⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage ⁷⁾	V_F	$I_F = 1300 \text{ A}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	2.2	2.4	V
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2.4	2.6	V
Peak reverse recovery current	I_{RM}		$T_{vj} = 25 \text{ }^\circ\text{C}$	1800		A
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2200		A
Recovered charge	Q_r	$V_{CC} = 2800 \text{ V}$, $I_F = 1300 \text{ A}$, $V_{GE} = \pm 15 \text{ V}$, $R_G = 1.8 \text{ } \Omega$, $C_{GE} = 330 \text{ nF}$, $di/dt = 3.8 \text{ kA}/\mu\text{s}$ $L_\sigma = 200 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^\circ\text{C}$	1300		μC
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2300		μC
Reverse recovery time	t_{rr}		$T_{vj} = 25 \text{ }^\circ\text{C}$	1100		ns
			$T_{vj} = 125 \text{ }^\circ\text{C}$	2400		ns
Reverse recovery energy	E_{rec}		$T_{vj} = 25 \text{ }^\circ\text{C}$	2300		mJ
			$T_{vj} = 125 \text{ }^\circ\text{C}$	3800		mJ

⁶⁾ Characteristic values according to IEC 60747 - 2

⁷⁾ Forward voltage is given at chip level

Package properties

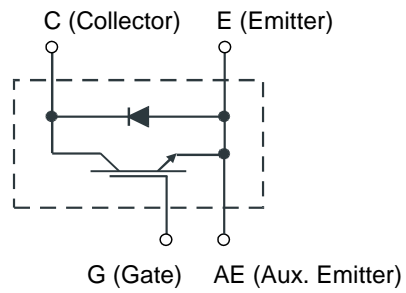
Parameter	Symbol	Conditions	min	typ	max	Unit
IGBT thermal resistance junction to case	$R_{th(j-c)IGBT}$				0.0063	K/W
Diode thermal resistance junction to case	$R_{th(j-c)DIODE}$				0.0060	K/W
IGBT thermal resistance ²⁾ case to heatsink	$R_{th(c-h)IGBT}$	Heatsink flatness : Complete module area < 100 μm Each submodule area < 20 μm Roughness : < 1.6 μm		0.0015		K/W
Diode thermal resistance ²⁾ case to heatsink	$R_{th(c-h)DIODE}$			0.0015		K/W
Comparative tracking index	CTI		600			

²⁾ for detailed mounting instructions refer to ABB Document No. 5SYA 2037-02

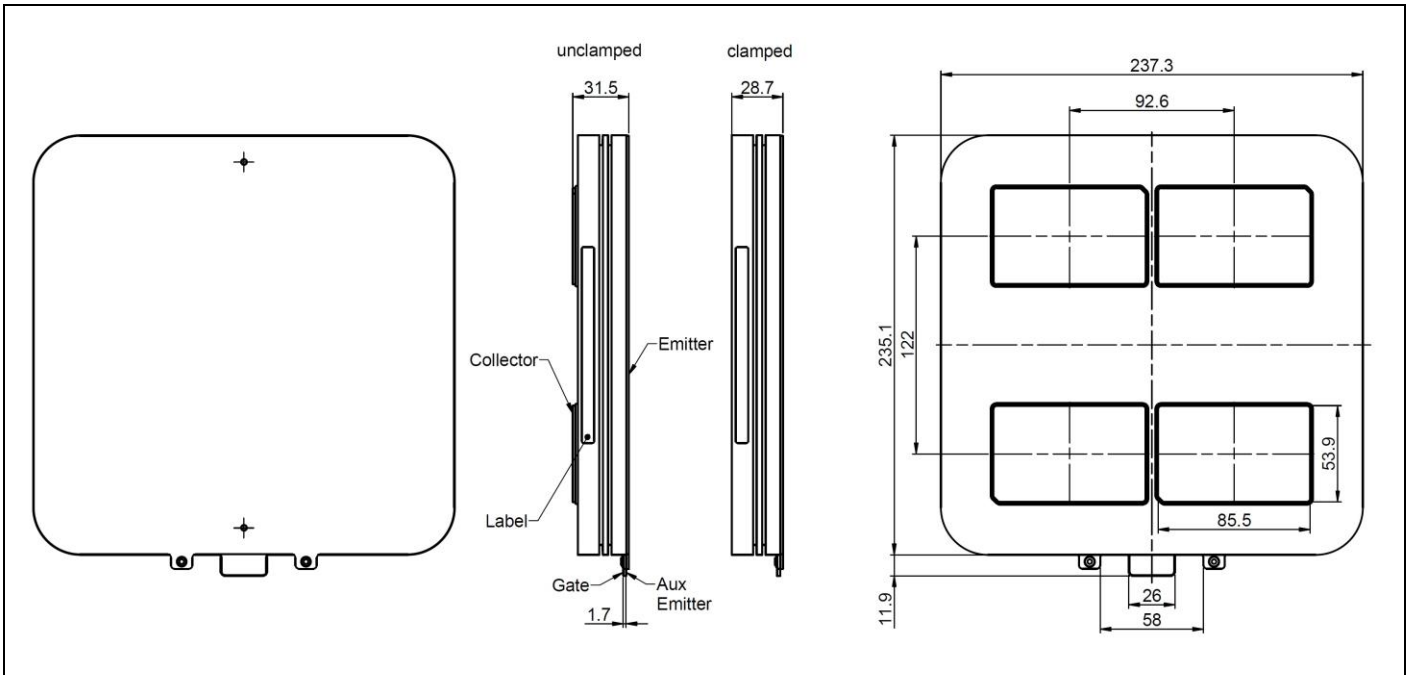
Mechanical properties

Parameter	Symbol	Conditions	min	typ	max	Unit
Dimensions	L x W x H	Typical	device clamped	246.95 x 237.3 x 28.75		mm
			device unclamped	246.95 x 237.3 x 31.5		
Clearance distance in air	d_a	according to IEC 60664-1 and EN 50124-1	23			mm
Surface creepage distance	d_s	according to IEC 60664-1 and EN 50124-1	40			mm
Mass	m			3700		g

Electrical configuration



Outline drawing ²⁾



Note: all dimensions are shown in millimeters

²⁾ For detailed mounting instructions refer to ABB Document No. 5SYA 2039

This is an electrostatic sensitive device; please observe the international standard IEC 60747-1, chap. VIII.
This product has been designed and qualified for Industrial Level.

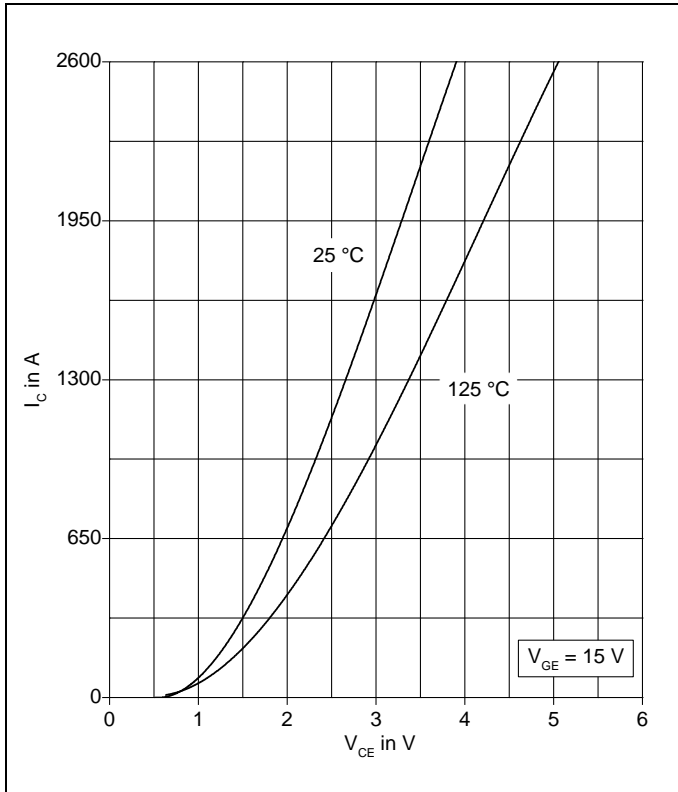


Fig. 1 Typical on-state characteristics, chip level

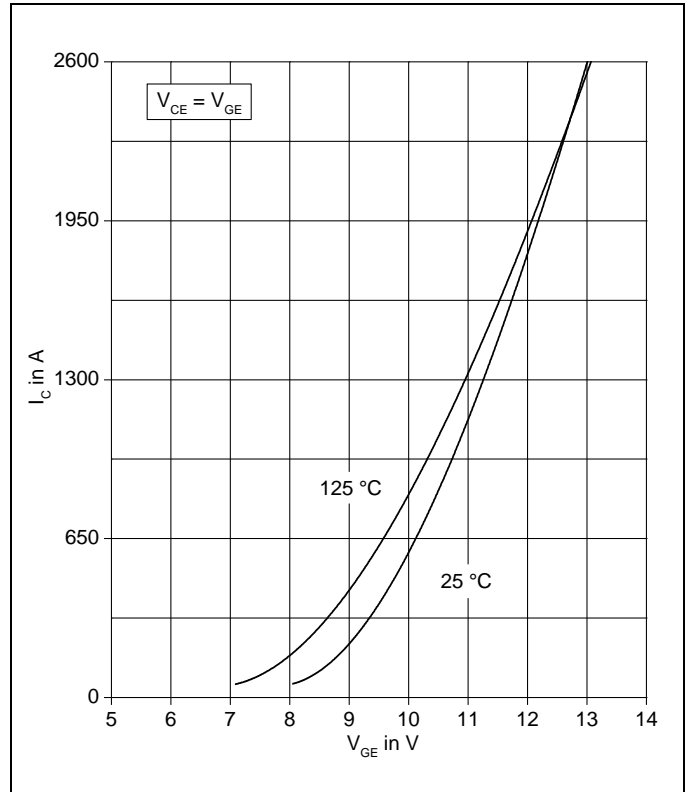


Fig. 2 Typical transfer characteristics, chip level

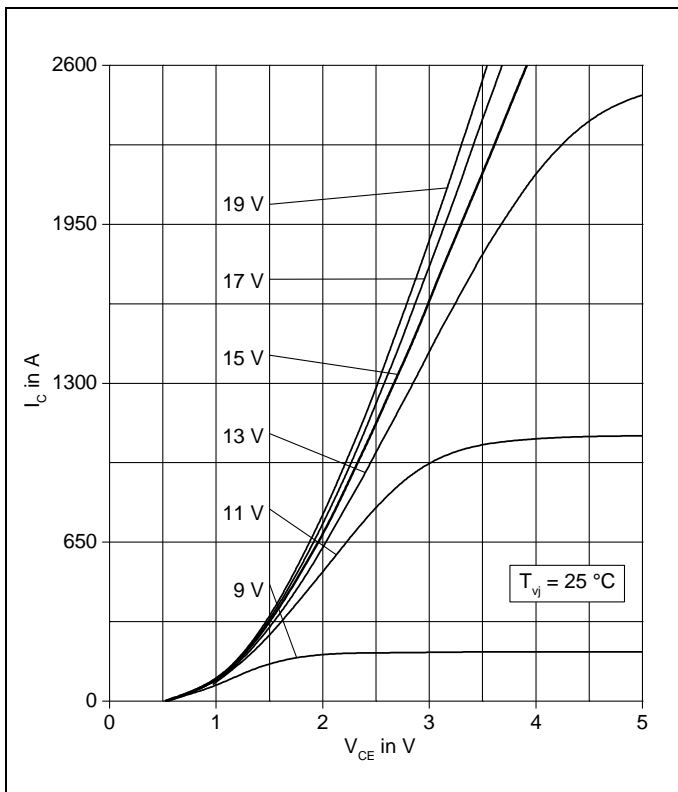


Fig. 3 Typical output characteristics, chip level

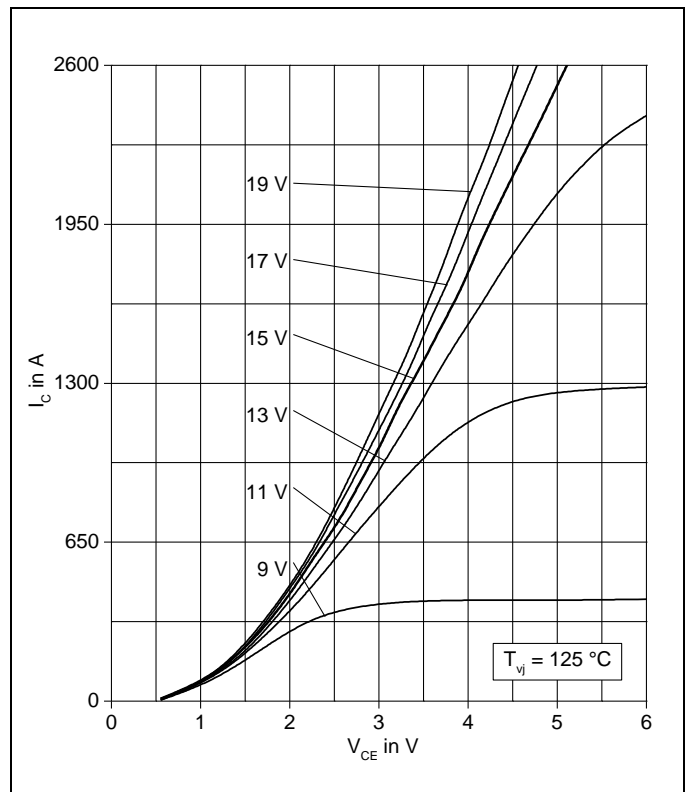


Fig. 4 Typical output characteristics, chip level

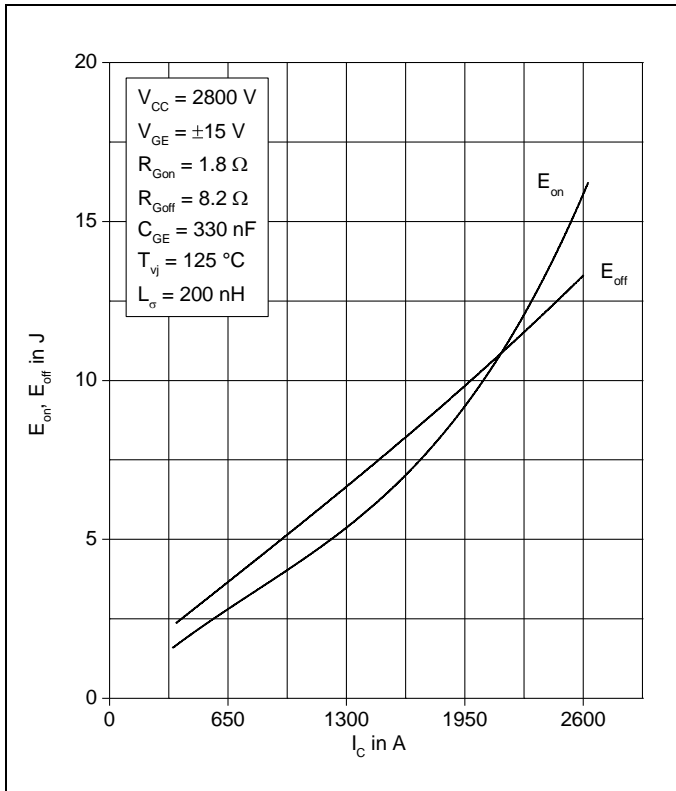


Fig. 5 Typical switching energies per pulse vs. collector current

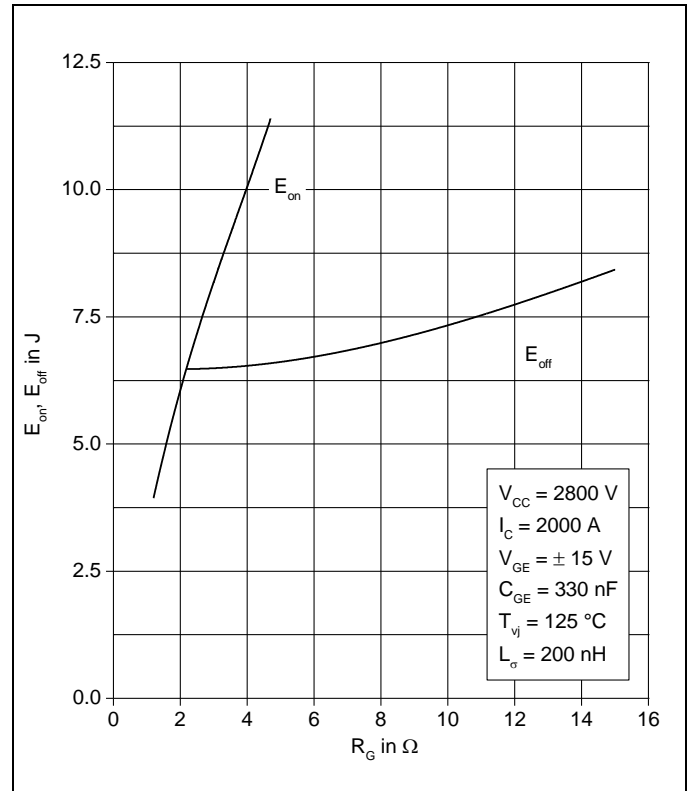


Fig. 6 Typical switching energies per pulse vs. gate resistor

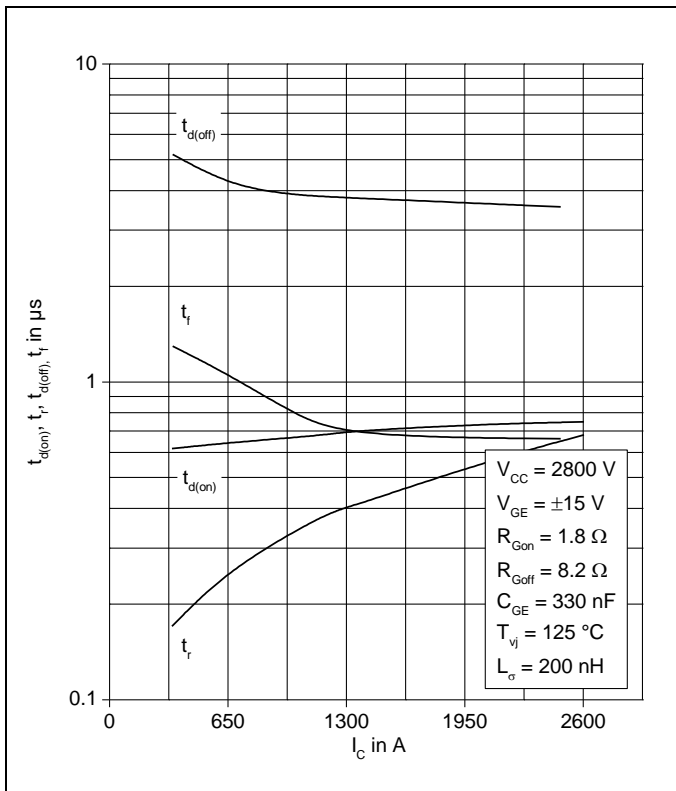


Fig. 7 Typical switching times vs. collector current

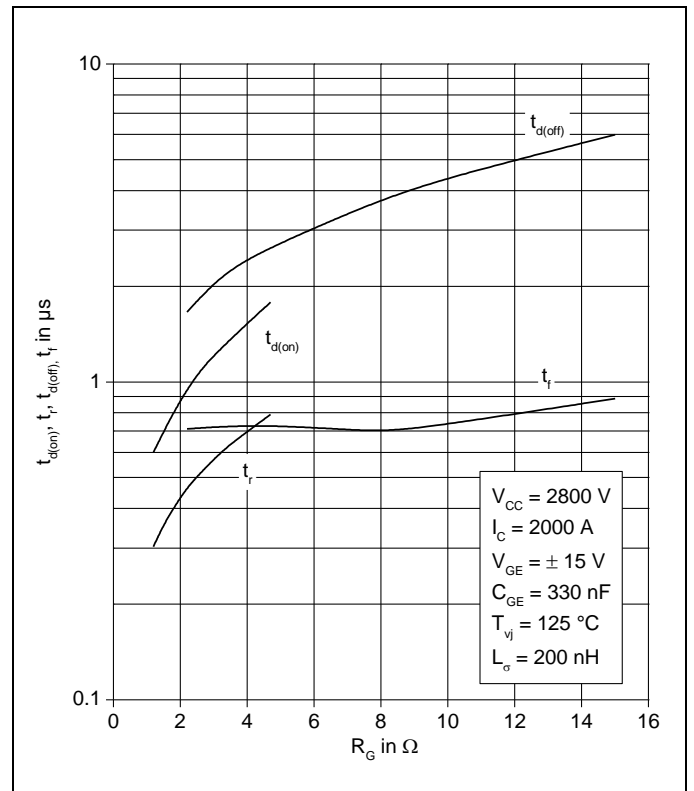


Fig. 8 Typical switching times vs. gate resistor

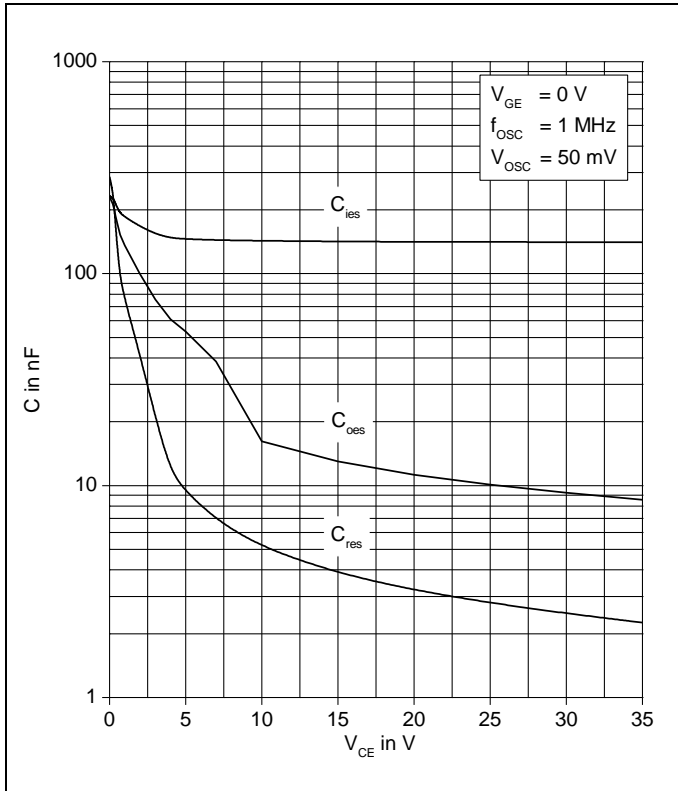


Fig. 9 Typical capacitances vs. collector-emitter voltage

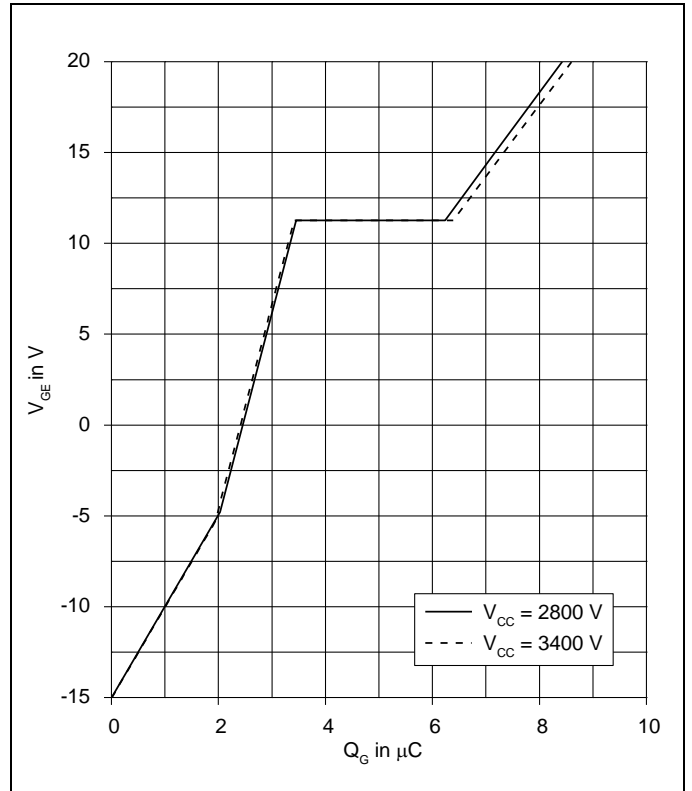


Fig. 10 Typical gate charge characteristics

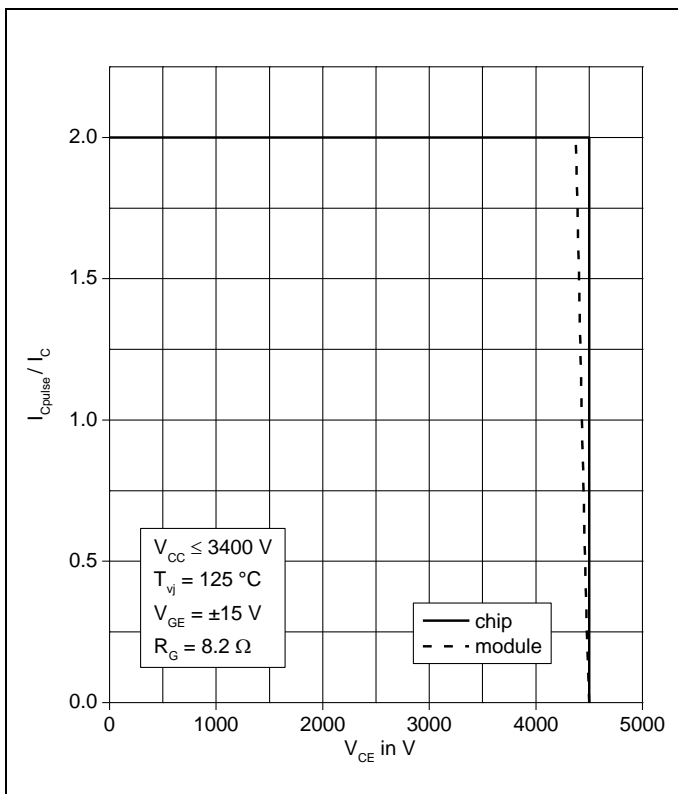


Fig. 11 Turn-off safe operating area (RBSOA)

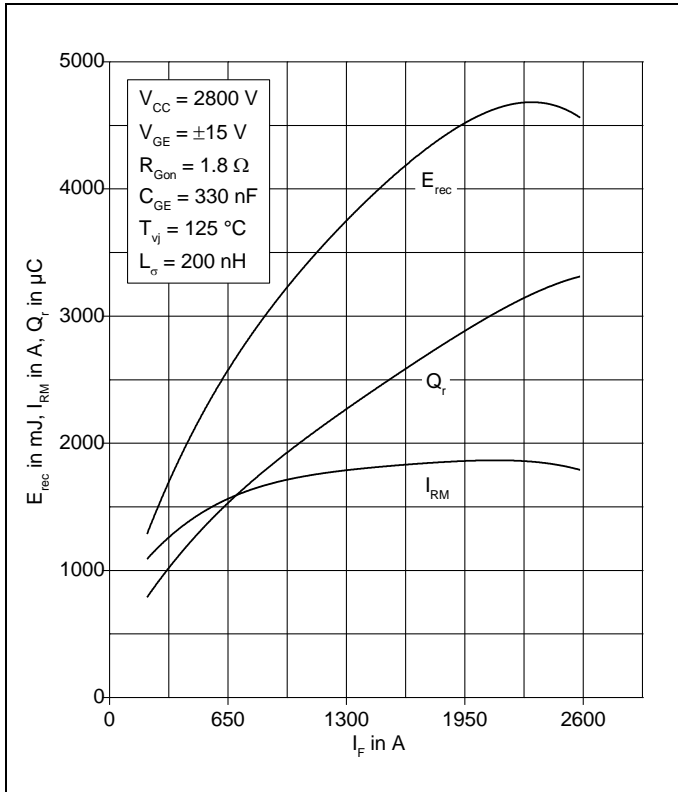


Fig. 12 Typical reverse recovery characteristics vs. forward current

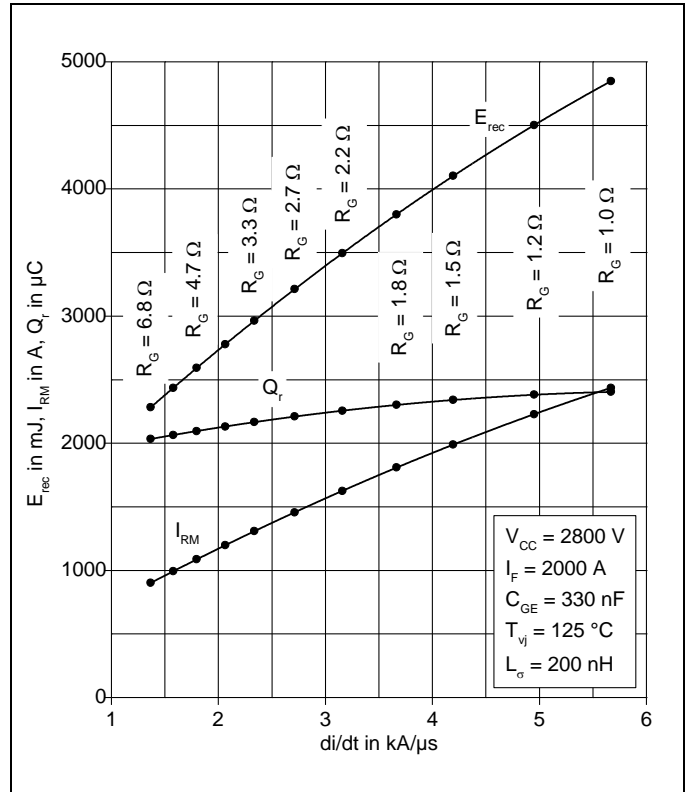


Fig. 13 Typical reverse recovery characteristics vs. di/dt

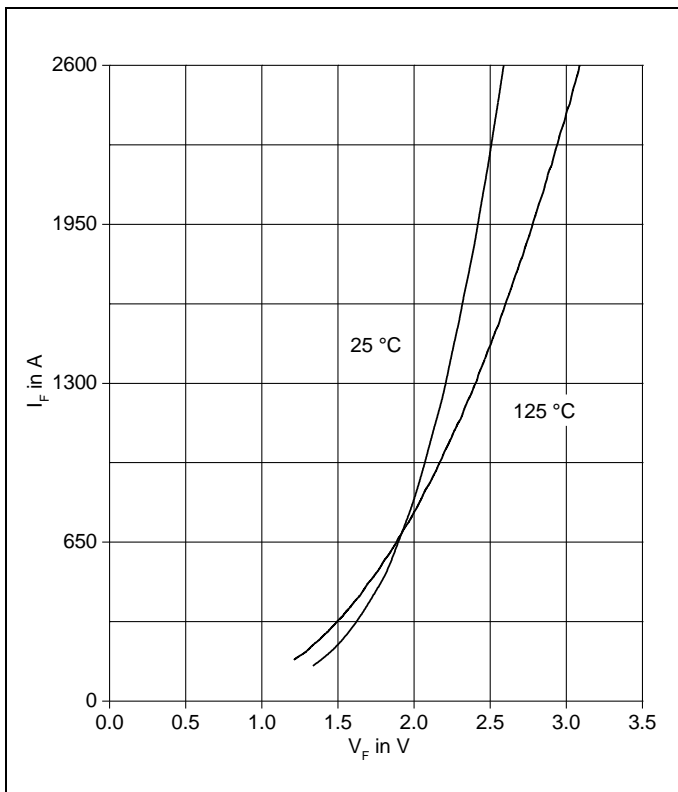


Fig. 14 Typical diode forward characteristics chip level

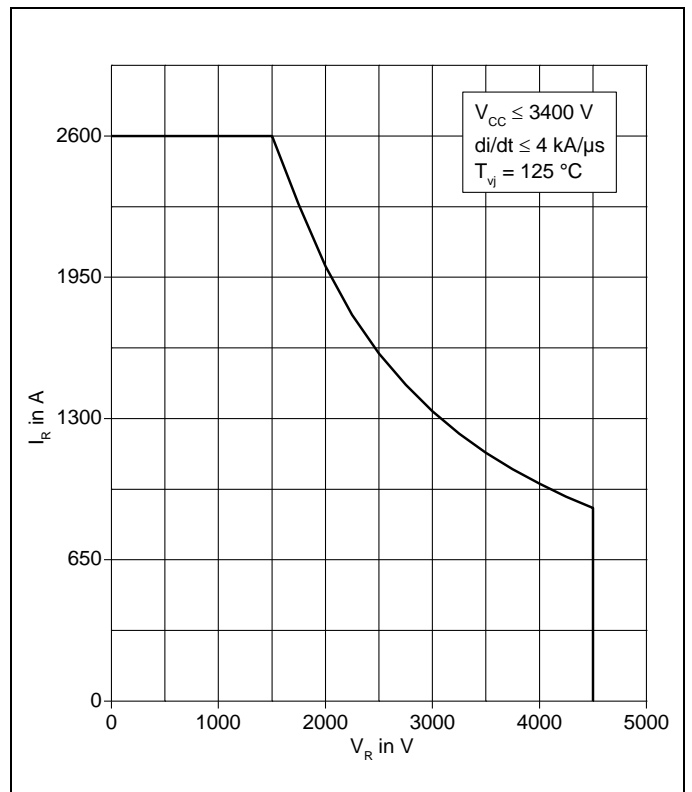


Fig. 15 Safe operating area diode (SOA)

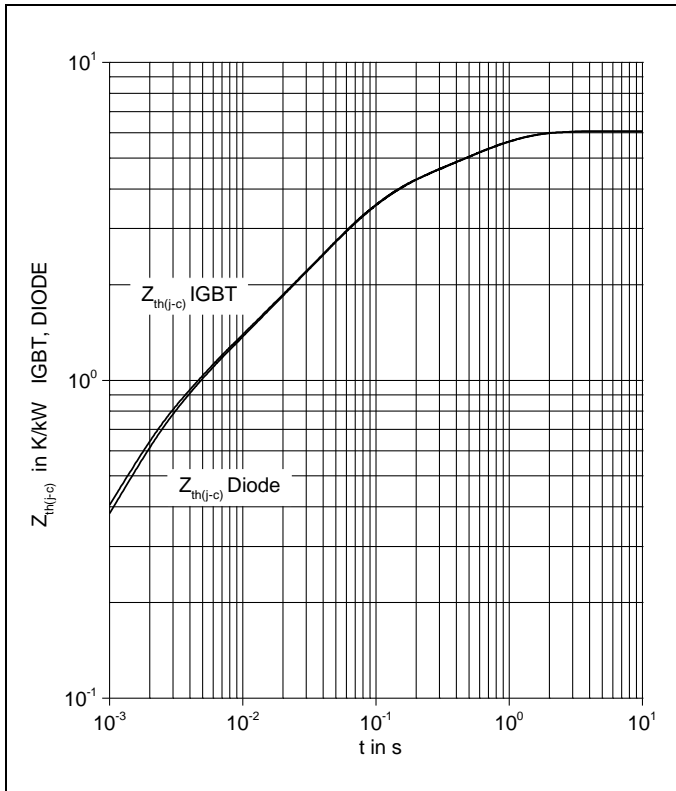


Fig. 16 Thermal impedance vs. time

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

i	1	2	3	4	5
IGBT R _i in K/kW	2.402	2.648	0.537	0.492	
IGBT τ _i in s	0.581	0.059	0.006	0.001	
DIODE R _i in K/kW	2.409	2.639	0.536	0.485	
DIODE τ _i in s	0.584	0.059	0.006	0.001	

Related documents:

- 5SYA 2045 Thermal runaway during blocking
- 5SYA 2053 Applying IGBT
- 5SYA 2093 Thermal design of IGBT modules

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